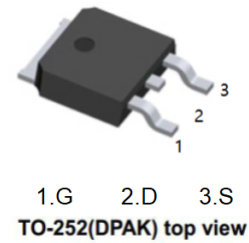


General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$ and fast switching speed.

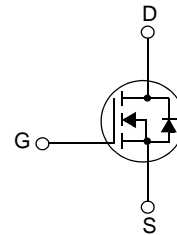


Application

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture

Features

- $V_{DS}(V) = 20V$
- $I_D = 35A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 5.5m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 8.5m\Omega$ ($V_{GS} = 4.5V$)
- Low gate charge: $Q_{g(TOT)} = 34nC(Typ)$, $V_{GS} = 10V$
- Low gate resistance



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	20	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous (Package Limited)	35	A
	-Continuous (Die Limited)	93	
	-Pulsed (Note 1)	354	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	144	mJ
P_D	Power Dissipation	77	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	$^\circ C$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case TO-252	1.94	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252	100	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in ² copper pad area	52	$^\circ C/W$

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		14.6		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{V}$,			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.2	1.6	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-6.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 35\text{A}$		4.0	5.5	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 33\text{A}$		5.7	8.5	
		$V_{GS} = 10\text{V}, I_D = 35\text{A}$ $T_J = 175^\circ\text{C}$		6.5	8.9	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 35\text{A}$		175		S
C_{iss}	Input Capacitance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1865	2480	pF
C_{oss}	Output Capacitance			550	730	pF
C_{rss}	Reverse Transfer Capacitance			335	445	pF
R_g	Gate Resistance		$f = 1\text{MHz}$		1.2	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{V}, I_D = 35\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 10\Omega$		9	18	ns
t_r	Rise Time			11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			47	75	ns
t_f	Fall Time			25	40	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V		$V_{GS} = 0\text{V}$ to 10V		34	48
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V}$ to 5V	$V_{DD} = 10\text{V}$ $I_D = 35\text{A}$ $I_g = 1.0\text{mA}$	16	22	nC
Q_{gs}	Gate to Source Gate Charge			3.2		nC
Q_{gd}	Gate to Drain "Miller" Charge			5.9		nC
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 35\text{A}$			0.89	1.25
		$V_{GS} = 0\text{V}, I_S = 15\text{A}$		0.82	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$		30	45	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$		23	35	nC

Notes:

- 1: Pulse time < 300 μs , Duty cycle = 2%.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.3\text{mH}$, $I_{AS} = 31\text{A}$, $V_{DD} = 18\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

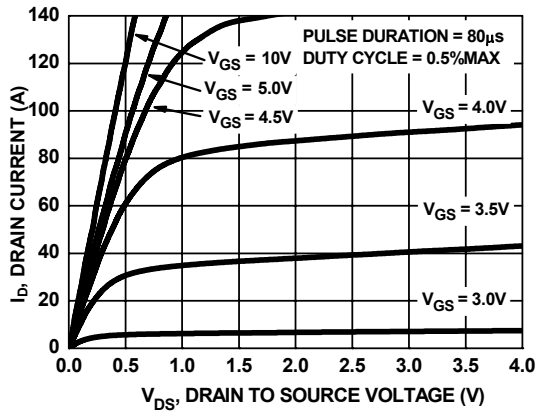


Figure 1. On Region Characteristics

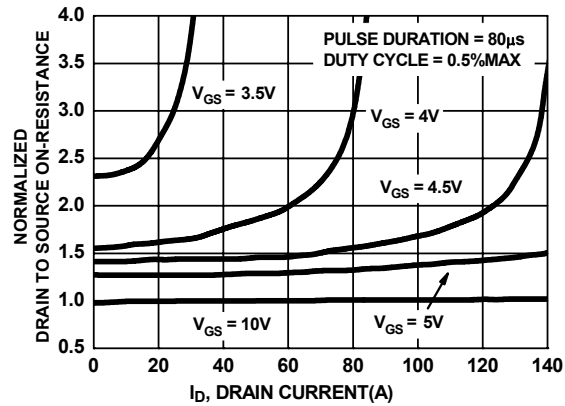


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

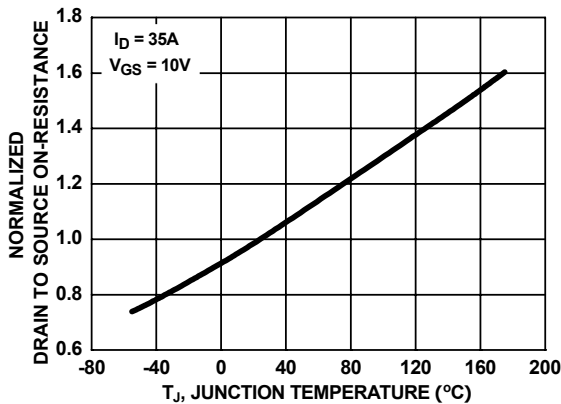


Figure 3. Normalized On Resistance vs Junction Temperature

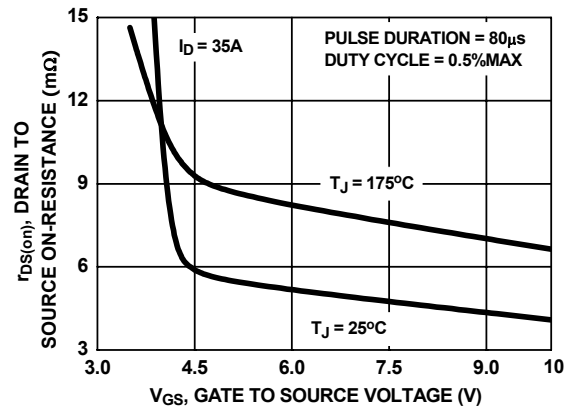


Figure 4. On-Resistance vs Gate to Source Voltage

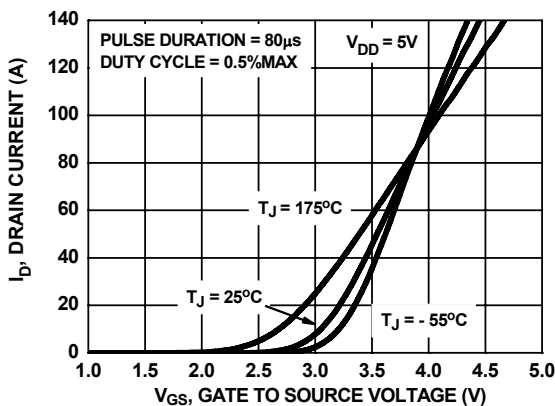


Figure 5. Transfer Characteristics

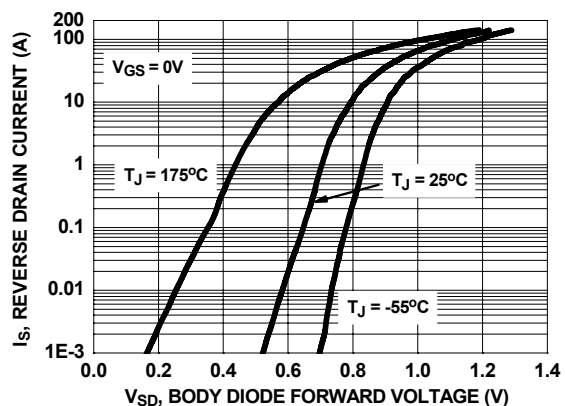


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

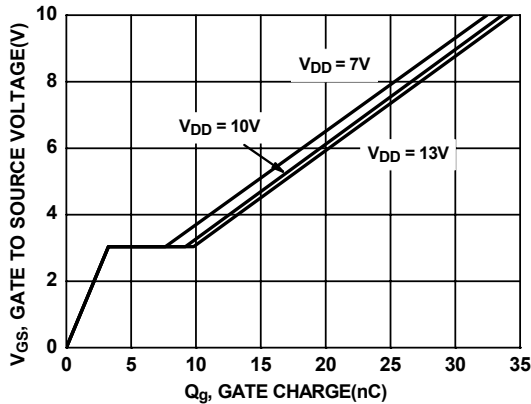


Figure 7. Gate Charge Characteristics

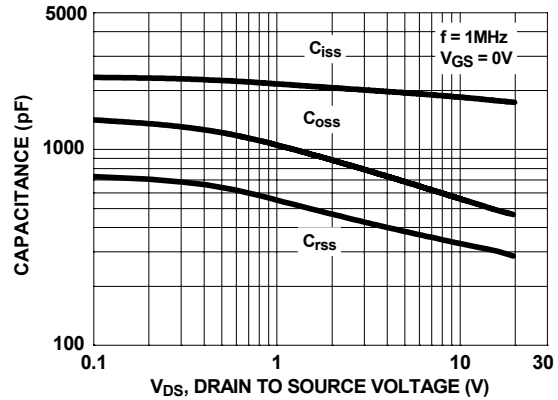


Figure 8. Capacitance vs Drain to Source Voltage

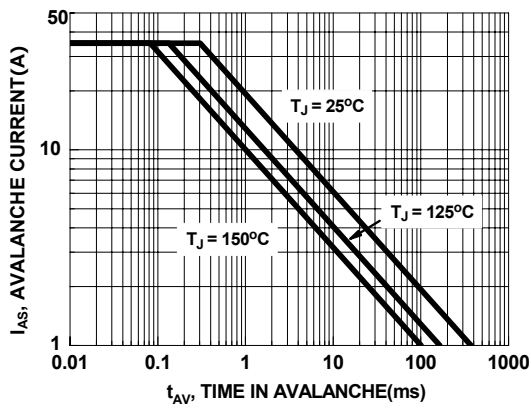


Figure 9. Unclamped Inductive Switching Capability

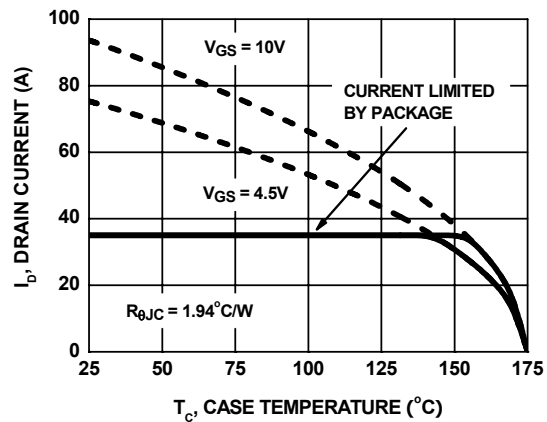


Figure 10. Maximum Continuous Drain Current vs Case Temperature

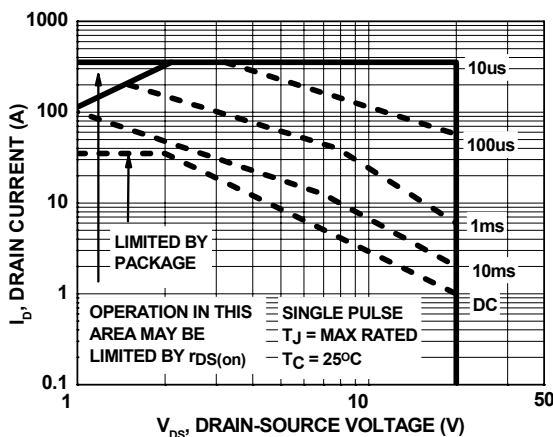


Figure 11. Forward Bias Safe Operating Area

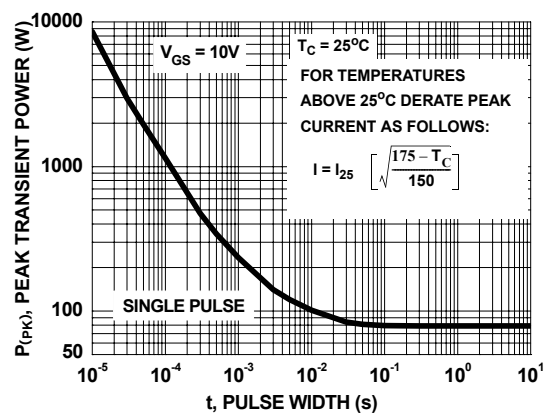


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

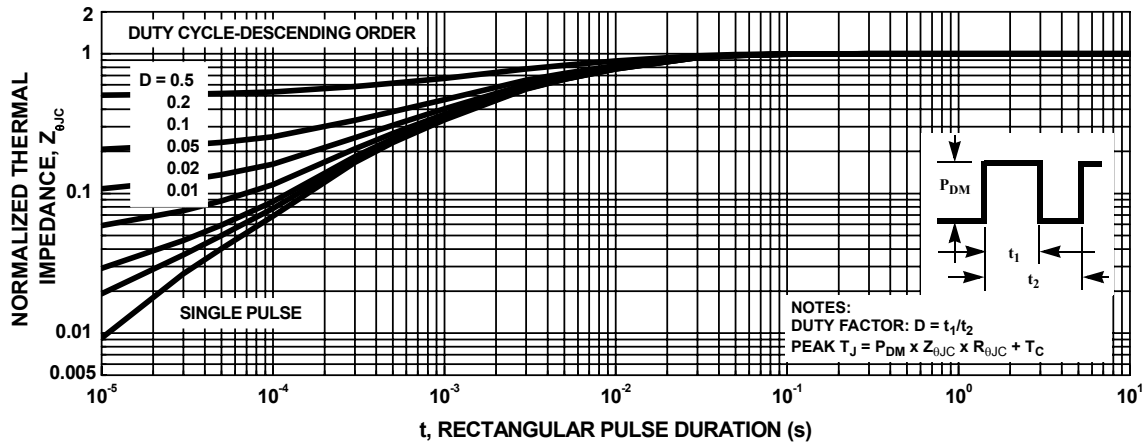
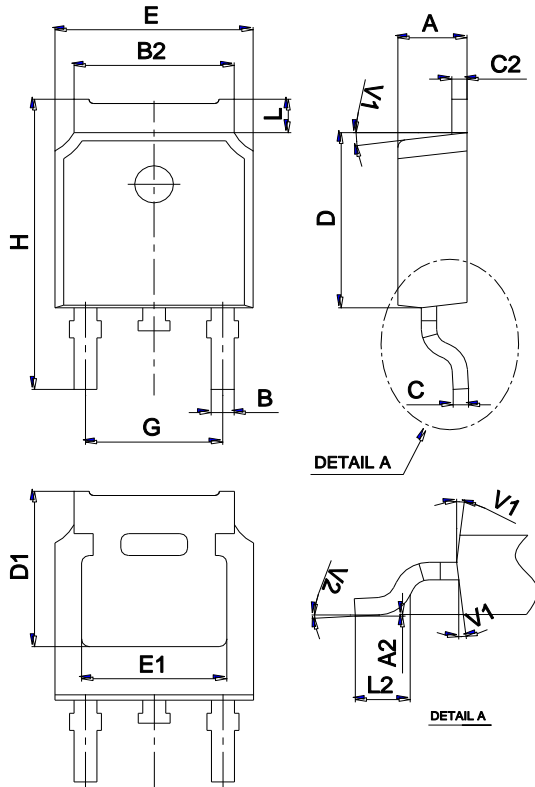


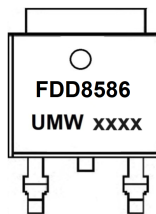
Figure 13. Transient Thermal Response Curve

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDD8586	TO-252	2500	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)